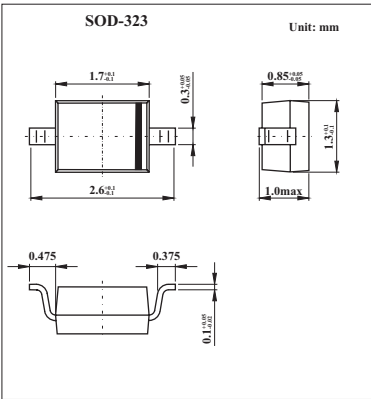


Silicon Epitaxial Planar Diode

1SV230

■ Features

- High Capacitance Ratio: $C_{2V}/C_{20V} = 8(\text{Typ.})$
- Low Series Resistance: $r_s = 0.73 \Omega (\text{Typ.})$
- Useful for small size Tuner.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35($R_L = 10 \text{ K } \Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	I_R	$V_R = 28 \text{ V}$			10	nA
Capacitance	C_{2V}	$f = 1 \text{ MHz}; V_R = 2 \text{ V}$	13.9	15	16.1	pF
	C_{20V}	$f = 1 \text{ MHz}; V_R = 20 \text{ V}$	1.7	1.9	2.1	
Capacitance Ratio	C_{2V}/C_{20V}		7.1	8		
Series Resistance	r_s	$V_R = 5 \text{ V}, f = 470 \text{ MHz}$		0.73	0.9	Ω

■ Marking

Marking	T7
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